

① 0 Ch. 4, Q. 5

With thermal conduction, \bar{e} 's at one end of the sample have more energy than \bar{e} 's at the other end. More energetic \bar{e} 's diffuse down the T gradient, carrying a net energy flux.

On average, there is no particle or charge buildup which would be quite unfavorable energetically.

② 0 Ch. 4, Q. 8

The Hall constant is defined as

$R_H \equiv \frac{E_H}{J_x B}$, where E_H is the Hall field, B is the external magnetic field, and J_x is the current density. Since $J_x \sim N$, (\bar{e} conc'n)

$$R_H \sim \frac{1}{N}$$

③ 0. Ch. 4, Q. 9

Positive charge carriers

mean that $J_x = +Ne v_x$

$$\Downarrow$$
$$R_H = \frac{E_H}{J_x B} \sim + \frac{1}{e} > 0$$

④ 0 Ch. 5, Q. 1

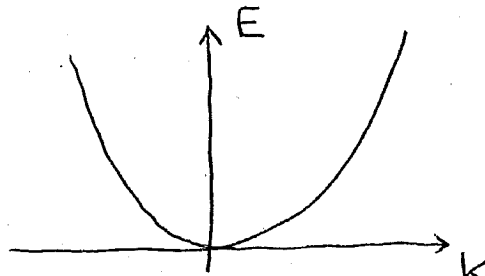
Here we must distinguish between core (localized) and valence (delocalized) \bar{e} 's. The combination of the core \bar{e} 's & the ions produces weak periodic pseudopotential. In other words, core \bar{e} 's "screen" the ions. Bloch's theorem states that the periodic nature of the resulting potential leads to valence \bar{e} 's with propagating (delocalized) wavefunctions. Thus there is no paradox - rather there are 2 types of \bar{e} 's.

⑤ 0 Ch. 5, Q. 2

For a truly free \bar{e} ,

$$\begin{cases} \psi_k^{(0)} = \frac{1}{\sqrt{L}} e^{ikx} \\ E_k^{(0)} = \frac{\hbar^2 k^2}{2m_0} \end{cases}, \quad \leftarrow \textcircled{1d}$$

This leads to a single dispersion curve:



"Cutting & pasting" is not justifiable here because there is no periodicity of the lattice:

$$E_k = E_{k+G}, \quad G = \frac{2\pi n}{a}, \quad n = 0, \pm 1, \pm 2, \dots$$

Thus the difference between empty lattice & free space is that we impose symmetry properties in k -space (even though there is no potential) in the former case. These symmetries follow from the translational symmetry of the real lattice. / 4

6. @ Ch. 4, Pr. 10

$$\nu_c = \frac{\omega_c}{2\pi} = 2.8 B \text{ GHz for } m^* = m_0, \text{ the free } \bar{e} \text{ mass.}$$

↑
in kG

Then $\nu_c = 24 \text{ GHz}$ gives

$$B = \frac{24}{2.8} \approx 8.6 \text{ kG.}$$

7. @ Ch. 5, Pr. 14

a) Free \bar{e} model:

$$n = \underset{\substack{\uparrow \\ \text{spin}}}{2} \frac{1}{(2\pi)^3} \frac{4}{3} \pi k_F^3 = \frac{1}{3\pi^2} k_F^3, \text{ or}$$

$$k_F = (3\pi^2 n)^{1/3}$$

b) Fermi sphere will touch the face of the 1st BZ when

$k_F = k_i$, where

$\vec{k}_i = \frac{1}{2} \vec{a}$ for fcc, and
(or $\frac{1}{2} \vec{b}$, $\frac{1}{2} \vec{c}$)

$$\left\{ \begin{array}{l} \vec{a} = \frac{2\pi}{a} (1, -1, 1) \\ \vec{b} = \frac{2\pi}{a} (1, 1, -1) \\ \vec{c} = \frac{2\pi}{a} (-1, 1, 1) \end{array} \right.$$

8. Kittel Pr. 6

The central equation is

$$(\lambda_k - \epsilon) C_k + \sum_G U_G C_{k-G} = 0$$

We recall that

$$\lambda_k = \frac{\hbar^2 k^2}{2m}$$

$$U(x) = \sum_G U_G e^{i\vec{G}\cdot\vec{x}}$$

\Downarrow

$$U_G = \frac{1}{a^2} \int_{\text{cell}} U(x) e^{-i\vec{G}\cdot\vec{x}} dx dy$$

$$\vec{x} = \{x, y\} \equiv (x_1, x_2)$$

$$\vec{G} = \left(\frac{2\pi}{a}, \frac{2\pi}{a} \right)$$

Then

$$U_G = - \frac{4u}{a^2} \prod_{i=1}^2 \int_0^a dx_i \cos\left(\frac{2\pi x_i}{a}\right) e^{-i\frac{2\pi x_i}{a}} =$$

$$= - \frac{4u}{a^2} \prod_{i=1}^2 \int_0^a dx_i \frac{e^{i\frac{2\pi x_i}{a}} + e^{-i\frac{2\pi x_i}{a}}}{2} e^{-i\frac{2\pi x_i}{a}} =$$

$$= - \frac{u}{a^2} \times a \times a = -u$$

\nearrow
using $e^{2\pi i n} = 1$

Then the central eq'n is:

$$\begin{bmatrix} \lambda_k - \epsilon & -u \\ -u & \lambda_{k-G} - \epsilon \end{bmatrix} \begin{bmatrix} c_k \\ c_{k-G} \end{bmatrix} = 0$$

$$\det [] = 0 \Rightarrow (\lambda_k - \epsilon)(\lambda_{k-G} - \epsilon) - u^2 = 0$$

$$\vec{k} = \left(\frac{\pi}{a}, \frac{\pi}{a} \right) \Rightarrow \vec{k} - \vec{G} = \left(-\frac{\pi}{a}, -\frac{\pi}{a} \right)$$

$$\vec{G} = \left(\frac{2\pi}{a}, \frac{2\pi}{a} \right)$$

$$\Downarrow \\ \lambda_k = \lambda_{k-G} \equiv \lambda$$

Hence $(\lambda - \epsilon)^2 = u^2$, or

$$\epsilon_{\pm} = \lambda \pm u$$

$$\text{gap} = \epsilon_+ - \epsilon_- = \underline{\underline{2u}}$$

9) Photonic crystals are devices in which a distribution of refractive indices is chosen such that incoming light waves become standing waves due to refraction & reflection. This makes them analogous to semiconductor devices, except light waves are used instead of e^- waves. Some of the challenges are:

- a) identifying & building structures of suitable materials out of them (with necessary optical properties)
- b) the devices must be able to handle incoming waves coming in all directions

Potential uses: lasers, fiber optics